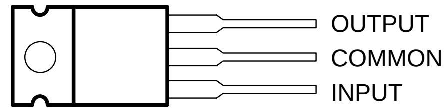
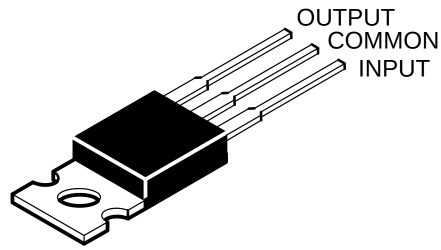
- **3-Terminal Regulators**
- **Output Current up to 500 mA**
- **No External Components**
- **Internal Thermal-Overload Protection**
- **High Power-Dissipation Capability**
- **Internal Short-Circuit Current Limiting**
- **Output Transistor Safe-Area Compensation**
- **Direct Replacements for Fairchild μA78M00 Series**

KC PACKAGE
(TOP VIEW)

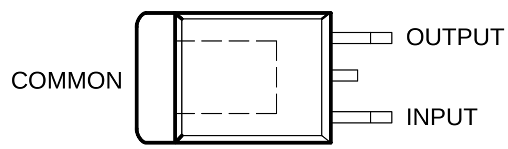


The COMMON terminal is in electrical contact with the mounting base.

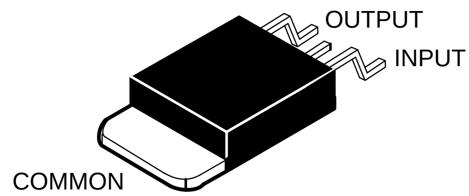
TO-220AB



KTP PACKAGE
(TOP VIEW)



The COMMON terminal is in electrical contact with the mounting base.



description

This series of fixed-voltage integrated-circuit voltage regulators is designed for a wide range of applications. These applications include on-card regulation for elimination of noise and distribution problems associated with single-point regulation. Each of these regulators can deliver up to 500 mA of output current. The internal current-limiting and thermal-shutdown features of these regulators essentially make them immune to overload. In addition to use as fixed-voltage regulators, these devices can be used with external components to obtain adjustable output voltages and currents and also as the power-pass element in precision regulators.

The μA78M00C series is characterized for operation over the virtual junction temperature range of 0°C to 125°C.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

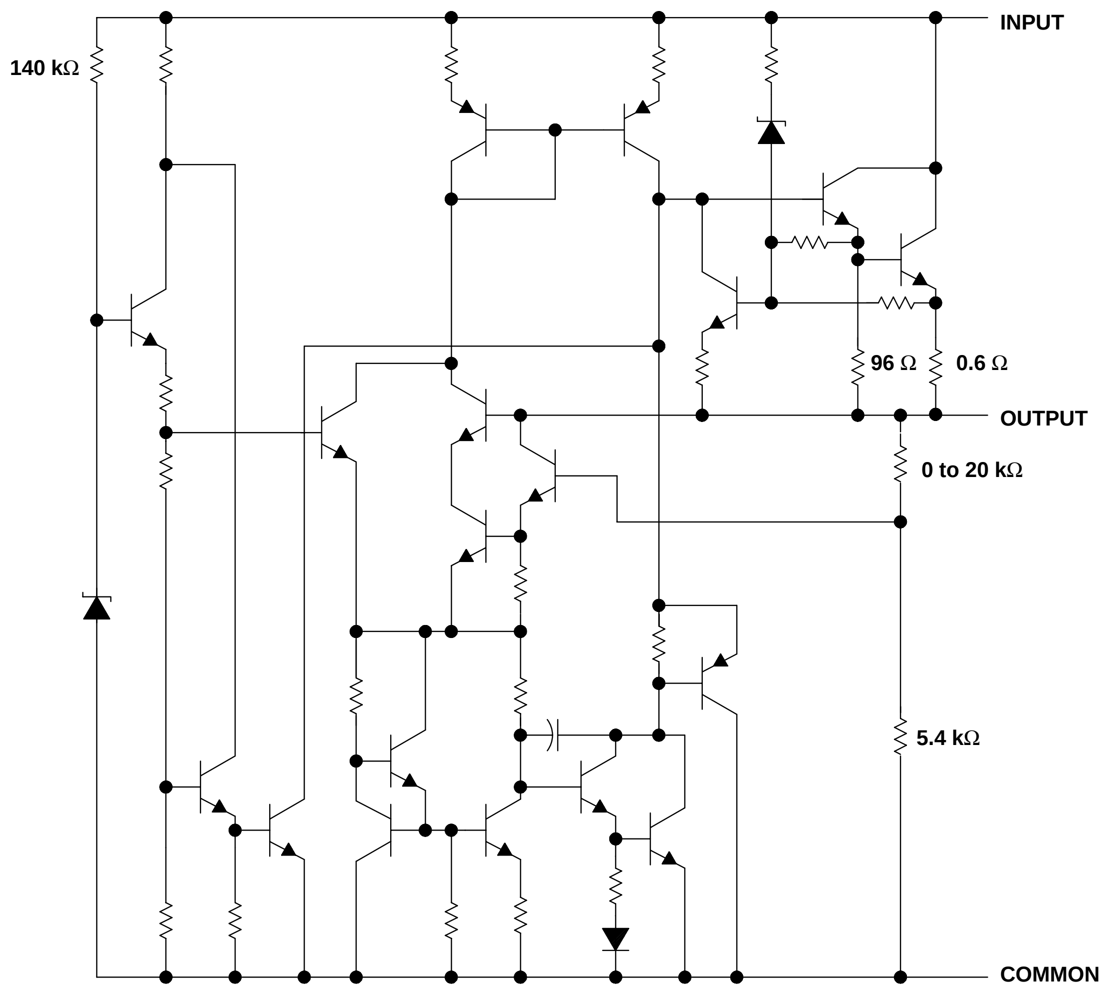
Copyright © 2001, Texas Instruments Incorporated

AVAILABLE OPTIONS

T_J	V_O(NOM) (V)	PACKAGED DEVICES	
		HEAT-SINK MOUNTED (KC)	PLASTIC FLANGE MOUNTED (KTP)
0°C to 125°C	5	μA78M05CKC	μA78M05CKTP
	6	μA78M06CKC	μA78M06CKTP
	8	μA78M08CKC	μA78M08CKTP
	9	μA78M09CKC	μA78M09CKTP
	10	μA78M10CKC	μA78M10CKTP
	12	μA78M12CKC	μA78M12CKTP
	15	μA78M15CKC	μA78M15CKTP

The KTP package is only available taped and reeled. Add the suffix R to the device type (e.g., μA78M05CKTPR).

schematic



Resistor values shown are nominal.

absolute maximum ratings over virtual junction temperature range (unless otherwise noted)†

Input voltage, V_I . . . . 35 V
Package thermal impedance, θ_{JA} (see Notes 1 and 2): KC package . . . . 22°C/W
KTP package . . . . 28°C/W
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds . . . . 260°C
Virtual junction temperature range, T_J . . . . 0°C to 150°C
Storage temperature range, T_{stg} . . . . –65°C to 150°C

† Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) – T_A)/\theta_{JA}$. Selecting the maximum of 150°C can impact reliability.
2. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions

			MIN	MAX	UNIT
V_I	Input voltage	μA78M05	7	25	V
		μA78M06	8	25	
		μA78M08	10.5	25	
		μA78M09	11.5	26	
		μA78M10	12.5	28	
		μA78M12	14.5	30	
		μA78M15	17.5	30	
I_O	Output current			500	mA
T_J	Operating virtual junction temperature		0	125	°C

electrical characteristics at specified virtual junction temperature, V_I = 10 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†		μA78M05C MIN	TYP	MAX	UNIT
Output voltage	V_I = 7 V to 20 V		4.8	5	5.2	V
		T_J = 0°C to 125°C	4.75		5.25	
Input voltage regulation	I_O = 200 mA	V_I = 7 V to 25 V		3	100	mV
		V_I = 8 V to 20 V				
		V_I = 8 V to 25 V		1	50	
Ripple rejection	V_I = 8 V to 18 V, f = 120 Hz	I_O = 100 mA, T_J = 0°C to 125°C	62			dB
		I_O = 300 mA	62	80		
Output voltage regulation	I_O = 5 mA to 500 mA			20	100	mV
	I_O = 5 mA to 200 mA			10	50	
Temperature coefficient of output voltage	I_O = 5 mA,	T_J = 0°C to 125°C		–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz			40	200	μV
Dropout voltage				2		V
Bias current				4.5	6	mA
Bias current change	I_O = 200 mA,	V_I = 8 V to 25 V, T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA	T_J = 0°C to 125°C			0.5	
Short-circuit output current	V_I = 35 V			300		mA
Peak output current				0.7		A

† All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 11 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			μA78M06C MIN	TYP	MAX	UNIT
Output voltage	I_O = 5 mA to 350 mA,	V_I = 8 V to 21 V		5.75	6	6.25	V
			T_J = 0°C to 125°C	5.7		6.3	
Input voltage regulation	I_O = 200 mA	V_I = 8 V to 25 V			5	100	mV
		V_I = 9 V to 25 V			1.5	50	
Ripple rejection	V_I = 9 V to 19 V,	f = 120 Hz	I_O = 100 mA, T_J = 0°C to 125°C	59			dB
			I_O = 300 mA	59	80		
Output voltage regulation	I_O = 5 mA to 500 mA				20	120	mV
	I_O = 5 mA to 200 mA				10	60	
Temperature coefficient of output voltage	I_O = 5 mA,	T_J = 0°C to 125°C			–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				45		μV
Dropout voltage					2		V
Bias current					4.5	6	mA
Bias current change	V_I = 9 V to 25 V,	I_O = 200 mA,	T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA,	T_J = 0°C to 125°C				0.5	
Short-circuit output current	V_I = 35 V				270		mA
Peak output current					0.7		A

† All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 14 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			µA78M08C MIN	µA78M08C TYP	µA78M08C MAX	UNIT
Output voltage	V_I = 10.5 V to 23 V,	I_O = 5 mA to 350 mA		7.7	8	8.3	V
			T_J = 0°C to 125°C	7.6		8.4	
Input voltage regulation	I_O = 200 mA	V_I = 10.5 V to 25 V			6	100	mV
		V_I = 11 V to 25 V			2	50	
Ripple rejection	V_I = 11.5 V to 21.5 V, f = 120 Hz	I_O = 100 mA,	T_J = 0°C to 125°C	56			dB
		I_O = 300 mA		56	80		
Output voltage regulation	I_O = 5 mA to 500 mA				25	160	mV
	I_O = 5 mA to 200 mA				10	80	
Temperature coefficient of output voltage	I_O = 5 mA,	T_J = 0°C to 125°C			–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				52		µV
Dropout voltage					2		V
Bias current					4.6	6	mA
Bias current change	V_I = 10.5 V to 25 V,	I_O = 200 mA,	T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA,	T_J = 0°C to 125°C				0.5	
Short-circuit output current	V_I = 35 V				250		mA
Peak output current					0.7		A

† All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 16 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			µA78M09C MIN	µA78M09C TYP	µA78M09C MAX	UNIT
Output voltage	V_I = 11.5 V to 24 V,	I_O = 5 mA to 350 mA		8.6	9	9.4	V
			T_J = 0°C to 125°C	8.5		9.5	
Input voltage regulation	I_O = 200 mA	V_I = 11.5 V to 26 V			6	100	mV
		V_I = 12 V to 26 V			2	50	
Ripple rejection	V_I = 13 V to 23 V, f = 120 Hz	I_O = 100 mA,	T_J = 0°C to 125°C	56			dB
		I_O = 300 mA		56	80		
Output voltage regulation	I_O = 5 mA to 500 mA				25	180	mV
	I_O = 5 mA to 200 mA				10	90	
Temperature coefficient of output voltage	I_O = 5 mA,	T_J = 0°C to 125°C			–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				58		µV
Dropout voltage					2		V
Bias current					4.6	6	mA
Bias current change	V_I = 11.5 V to 26 V,	I_O = 200 mA,	T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA,	T_J = 0°C to 125°C				0.5	
Short-circuit output current	V_I = 35 V				250		mA
Peak output current					0.7		A

† All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 17 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			μA78M10C MIN	TYP	MAX	UNIT
Output voltage	V_I = 12.5 V to 25 V,	I_O = 5 mA to 350 mA		9.6	10	10.4	V
			T_J = 0°C to 125°C	9.5		10.5	
Input voltage regulation	I_O = 200 mA	V_I = 12.5 V to 28 V			7	100	mV
		V_I = 14 V to 28 V			2	50	
Ripple rejection	V_I = 15 V to 25 V, f = 120 Hz	I_O = 100 mA,	T_J = 0°C to 125°C	59			dB
		I_O = 300 mA		55	80		
Output voltage regulation	I_O = 5 mA to 500 mA				25	200	mV
	I_O = 5 mA to 200 mA				10	100	
Temperature coefficient of output voltage	I_O = 5 mA,	T_J = 0°C to 125°C			–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				64		μV
Dropout voltage					2		V
Bias current					4.7	6	mA
Bias current change	V_I = 12.5 V to 28 V,	I_O = 200 mA,	T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA,	T_J = 0°C to 125°C				0.5	
Short-circuit output current	V_I = 35 V				245		mA
Peak output current					0.7		A

† All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 19 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			μA78M12C MIN	TYP	MAX	UNIT
Output voltage	V_I = 14.5 V to 27 V,	I_O = 5 mA to 350 mA		11.5	12	12.5	V
			T_J = 0°C to 125°C	11.4		12.6	
Input voltage regulation	I_O = 200 mA	V_I = 14.5 V to 30 V			8	100	mV
		V_I = 16 V to 30 V			2	50	
Ripple rejection	V_I = 15 V to 25 V, f = 120 Hz	I_O = 100 mA,	T_J = 0°C to 125°C	55			dB
		I_O = 300 mA		55	80		
Output voltage regulation	I_O = 5 mA to 500 mA				25	240	mV
	I_O = 5 mA to 200 mA				10	120	
Temperature coefficient of output voltage	I_O = 5 mA				–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				75		μV
Dropout voltage					2		V
Bias current					4.8	6	mA
Bias current change	V_I = 14.5 V to 30 V,	I_O = 200 mA,	T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA,	T_J = 0°C to 125°C				0.5	
Short-circuit output current	V_I = 35 V				240		mA
Peak output current					0.7		A

† All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 23 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			μA78M15C MIN	μA78M15C TYP	μA78M15C MAX	UNIT
Output voltage	V_I = 17.5 V to 30 V,	I_O = 5 mA to 350 mA		14.4	15	15.6	V
			T_J = 0°C to 125°C	14.25		15.75	
Input voltage regulation	I_O = 200 mA	V_I = 17.5 V to 30 V			10	100	mV
		V_I = 20 V to 30 V			3	50	
Ripple rejection	V_I = 18.5 V to 28.5 V, f = 120 Hz	I_O = 100 mA,	T_J = 0°C to 125°C	54			dB
		I_O = 300 mA		54	70		
Output voltage regulation	I_O = 5 mA to 500 mA				25	300	mV
	I_O = 5 mA to 200 mA				10	150	
Temperature coefficient of output voltage	I_O = 5 mA,	T_J = 0°C to 125°C			–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				90		μV
Dropout voltage					2		V
Bias current					4.8	6	mA
Bias current change	V_I = 17.5 V to 30 V,	I_O = 200 mA,	T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA,	T_J = 0°C to 125°C				0.5	
Short-circuit output current	V_I = 35 V				240		mA
Peak output current					0.7		A

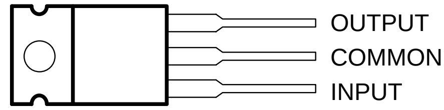
† All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

µA78M00 SERIES
POSITIVE-VOLTAGE REGULATORS

SLVS059E – JUNE 1976 – REVISED AUGUST 2001

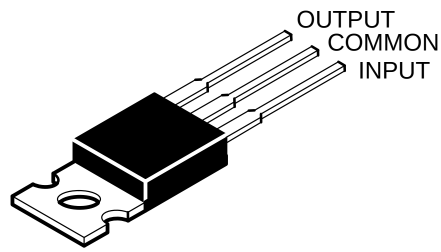
- **3-Terminal Regulators**
- **Output Current up to 500 mA**
- **No External Components**
- **Internal Thermal-Overload Protection**
- **High Power-Dissipation Capability**
- **Internal Short-Circuit Current Limiting**
- **Output Transistor Safe-Area Compensation**
- **Direct Replacements for Fairchild µA78M00 Series**

KC PACKAGE
(TOP VIEW)

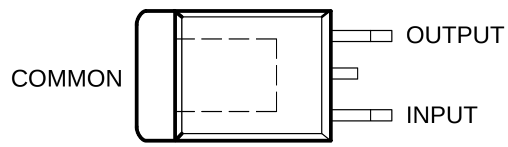


The COMMON terminal is in electrical contact with the mounting base.

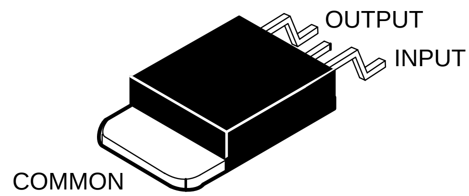
TO-220AB



KTP PACKAGE
(TOP VIEW)



The COMMON terminal is in electrical contact with the mounting base.



description

This series of fixed-voltage integrated-circuit voltage regulators is designed for a wide range of applications. These applications include on-card regulation for elimination of noise and distribution problems associated with single-point regulation. Each of these regulators can deliver up to 500 mA of output current. The internal current-limiting and thermal-shutdown features of these regulators essentially make them immune to overload. In addition to use as fixed-voltage regulators, these devices can be used with external components to obtain adjustable output voltages and currents and also as the power-pass element in precision regulators.

The µA78M00C series is characterized for operation over the virtual junction temperature range of 0°C to 125°C.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

PRODUCTION DATA information is current as of publication date. Products conform to specifications per the terms of Texas Instruments standard warranty. Production processing does not necessarily include testing of all parameters.

Copyright © 2001, Texas Instruments Incorporated

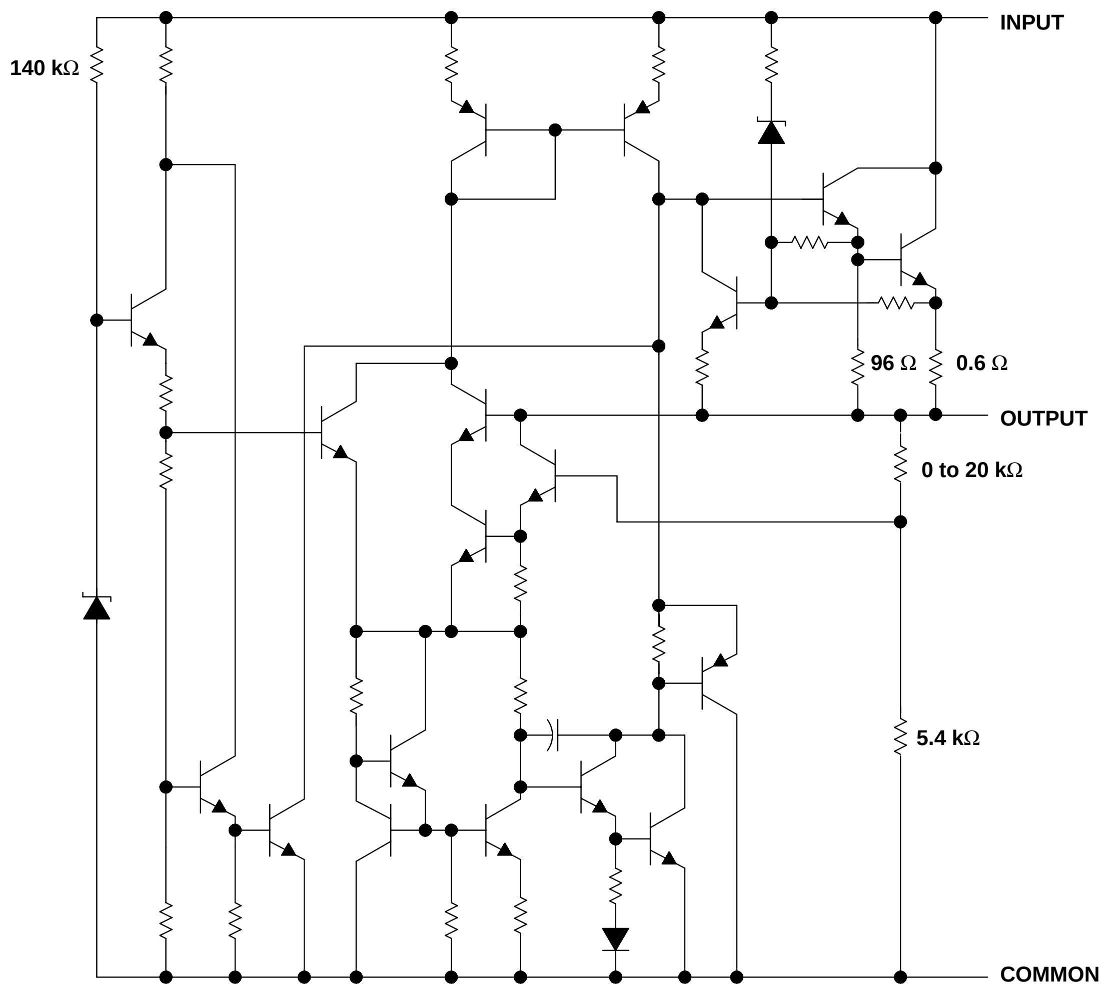
TEXAS INSTRUMENTS
POST OFFICE BOX 655303 • DALLAS, TEXAS 75265

AVAILABLE OPTIONS

T_J	V_O(NOM) (V)	PACKAGED DEVICES	
		HEAT-SINK MOUNTED (KC)	PLASTIC FLANGE MOUNTED (KTP)
0°C to 125°C	5	µA78M05CKC	µA78M05CKTP
	6	µA78M06CKC	µA78M06CKTP
	8	µA78M08CKC	µA78M08CKTP
	9	µA78M09CKC	µA78M09CKTP
	10	µA78M10CKC	µA78M10CKTP
	12	µA78M12CKC	µA78M12CKTP
	15	µA78M15CKC	µA78M15CKTP

The KTP package is only available taped and reeled. Add the suffix R to the device type (e.g., µA78M05CKTPR).

schematic



Resistor values shown are nominal.

absolute maximum ratings over virtual junction temperature range (unless otherwise noted)†

Input voltage, V_I . . . . . 35 V
Package thermal impedance, θ_{JA} (see Notes 1 and 2): KC package . . . . . 22°C/W
KTP package . . . . . 28°C/W
Lead temperature 1,6 mm (1/16 inch) from case for 10 seconds . . . . . 260°C
Virtual junction temperature range, T_J . . . . . 0°C to 150°C
Storage temperature range, T_{stg} . . . . . –65°C to 150°C

† Stresses beyond those listed under “absolute maximum ratings” may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under “recommended operating conditions” is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

NOTES: 1. Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is $P_D = (T_J(max) – T_A)/\theta_{JA}$. Selecting the maximum of 150°C can impact reliability.
2. The package thermal impedance is calculated in accordance with JESD 51-7.

recommended operating conditions

			MIN	MAX	UNIT
V_I	Input voltage	μA78M05	7	25	V
		μA78M06	8	25	
		μA78M08	10.5	25	
		μA78M09	11.5	26	
		μA78M10	12.5	28	
		μA78M12	14.5	30	
		μA78M15	17.5	30	
I_O	Output current			500	mA
T_J	Operating virtual junction temperature		0	125	°C

electrical characteristics at specified virtual junction temperature, V_I = 10 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†		μA78M05C MIN	μA78M05C TYP	μA78M05C MAX	UNIT
Output voltage	V_I = 7 V to 20 V		4.8	5	5.2	V
		T_J = 0°C to 125°C	4.75		5.25	
Input voltage regulation	I_O = 200 mA	V_I = 7 V to 25 V		3	100	mV
		V_I = 8 V to 20 V				
		V_I = 8 V to 25 V		1	50	
Ripple rejection	V_I = 8 V to 18 V, f = 120 Hz	I_O = 100 mA, T_J = 0°C to 125°C	62			dB
		I_O = 300 mA	62	80		
Output voltage regulation	I_O = 5 mA to 500 mA			20	100	mV
	I_O = 5 mA to 200 mA			10	50	
Temperature coefficient of output voltage	I_O = 5 mA,	T_J = 0°C to 125°C		–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz			40	200	μV
Dropout voltage				2		V
Bias current				4.5	6	mA
Bias current change	I_O = 200 mA,	V_I = 8 V to 25 V, T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA	T_J = 0°C to 125°C			0.5	
Short-circuit output current	V_I = 35 V			300		mA
Peak output current				0.7		A

† All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 11 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			μA78M06C MIN	μA78M06C TYP	μA78M06C MAX	UNIT
Output voltage	I_O = 5 mA to 350 mA,	V_I = 8 V to 21 V		5.75	6	6.25	V
			T_J = 0°C to 125°C	5.7		6.3	
Input voltage regulation	I_O = 200 mA	V_I = 8 V to 25 V			5	100	mV
		V_I = 9 V to 25 V			1.5	50	
Ripple rejection	V_I = 9 V to 19 V,	f = 120 Hz	I_O = 100 mA, T_J = 0°C to 125°C	59			dB
			I_O = 300 mA	59	80		
Output voltage regulation	I_O = 5 mA to 500 mA				20	120	mV
	I_O = 5 mA to 200 mA				10	60	
Temperature coefficient of output voltage	I_O = 5 mA,	T_J = 0°C to 125°C			–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				45		μV
Dropout voltage					2		V
Bias current					4.5	6	mA
Bias current change	V_I = 9 V to 25 V,	I_O = 200 mA,	T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA,	T_J = 0°C to 125°C				0.5	
Short-circuit output current	V_I = 35 V				270		mA
Peak output current					0.7		A

† All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 14 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			μA78M08C MIN	TYP	MAX	UNIT
Output voltage	V_I = 10.5 V to 23 V,	I_O = 5 mA to 350 mA		7.7	8	8.3	V
			T_J = 0°C to 125°C	7.6		8.4	
Input voltage regulation	I_O = 200 mA	V_I = 10.5 V to 25 V			6	100	mV
		V_I = 11 V to 25 V			2	50	
Ripple rejection	V_I = 11.5 V to 21.5 V, f = 120 Hz	I_O = 100 mA,	T_J = 0°C to 125°C	56			dB
		I_O = 300 mA		56	80		
Output voltage regulation	I_O = 5 mA to 500 mA				25	160	mV
	I_O = 5 mA to 200 mA				10	80	
Temperature coefficient of output voltage	I_O = 5 mA,	T_J = 0°C to 125°C			–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				52		μV
Dropout voltage					2		V
Bias current					4.6	6	mA
Bias current change	V_I = 10.5 V to 25 V,	I_O = 200 mA,	T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA,	T_J = 0°C to 125°C				0.5	
Short-circuit output current	V_I = 35 V				250		mA
Peak output current					0.7		A

† All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 16 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			μA78M09C MIN	TYP	MAX	UNIT
Output voltage	V_I = 11.5 V to 24 V,	I_O = 5 mA to 350 mA		8.6	9	9.4	V
			T_J = 0°C to 125°C	8.5		9.5	
Input voltage regulation	I_O = 200 mA	V_I = 11.5 V to 26 V			6	100	mV
		V_I = 12 V to 26 V			2	50	
Ripple rejection	V_I = 13 V to 23 V, f = 120 Hz	I_O = 100 mA,	T_J = 0°C to 125°C	56			dB
		I_O = 300 mA		56	80		
Output voltage regulation	I_O = 5 mA to 500 mA				25	180	mV
	I_O = 5 mA to 200 mA				10	90	
Temperature coefficient of output voltage	I_O = 5 mA,	T_J = 0°C to 125°C			–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				58		μV
Dropout voltage					2		V
Bias current					4.6	6	mA
Bias current change	V_I = 11.5 V to 26 V,	I_O = 200 mA,	T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA,	T_J = 0°C to 125°C				0.5	
Short-circuit output current	V_I = 35 V				250		mA
Peak output current					0.7		A

† All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, $V_I = 17$ V, $I_O = 350$ mA, $T_J = 25°C$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			μA78M10C MIN	μA78M10C TYP	μA78M10C MAX	UNIT
Output voltage	V_I = 12.5 V to 25 V,	I_O = 5 mA to 350 mA		9.6	10	10.4	V
			T_J = 0°C to 125°C	9.5		10.5	
Input voltage regulation	I_O = 200 mA	V_I = 12.5 V to 28 V			7	100	mV
		V_I = 14 V to 28 V			2	50	
Ripple rejection	V_I = 15 V to 25 V, f = 120 Hz	I_O = 100 mA,	T_J = 0°C to 125°C	59			dB
		I_O = 300 mA		55	80		
Output voltage regulation	I_O = 5 mA to 500 mA				25	200	mV
	I_O = 5 mA to 200 mA				10	100	
Temperature coefficient of output voltage	I_O = 5 mA,	T_J = 0°C to 125°C			–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				64		μV
Dropout voltage					2		V
Bias current					4.7	6	mA
Bias current change	V_I = 12.5 V to 28 V,	I_O = 200 mA,	T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA,	T_J = 0°C to 125°C				0.5	
Short-circuit output current	V_I = 35 V				245		mA
Peak output current					0.7		A

† All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, $V_I = 19$ V, $I_O = 350$ mA, $T_J = 25°C$ (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			μA78M12C MIN	μA78M12C TYP	μA78M12C MAX	UNIT
Output voltage	V_I = 14.5 V to 27 V,	I_O = 5 mA to 350 mA		11.5	12	12.5	V
			T_J = 0°C to 125°C	11.4		12.6	
Input voltage regulation	I_O = 200 mA	V_I = 14.5 V to 30 V			8	100	mV
		V_I = 16 V to 30 V			2	50	
Ripple rejection	V_I = 15 V to 25 V, f = 120 Hz	I_O = 100 mA,	T_J = 0°C to 125°C	55			dB
		I_O = 300 mA		55	80		
Output voltage regulation	I_O = 5 mA to 500 mA				25	240	mV
	I_O = 5 mA to 200 mA				10	120	
Temperature coefficient of output voltage	I_O = 5 mA				–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				75		μV
Dropout voltage					2		V
Bias current					4.8	6	mA
Bias current change	V_I = 14.5 V to 30 V,	I_O = 200 mA,	T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA,	T_J = 0°C to 125°C				0.5	
Short-circuit output current	V_I = 35 V				240		mA
Peak output current					0.7		A

† All characteristics are measured with a 0.33-μF capacitor across the input and a 0.1-μF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

electrical characteristics at specified virtual junction temperature, V_I = 23 V, I_O = 350 mA, T_J = 25°C (unless otherwise noted)

PARAMETER	TEST CONDITIONS†			µA78M15C MIN	µA78M15C TYP	µA78M15C MAX	UNIT
Output voltage	V_I = 17.5 V to 30 V,	I_O = 5 mA to 350 mA		14.4	15	15.6	V
			T_J = 0°C to 125°C	14.25		15.75	
Input voltage regulation	I_O = 200 mA	V_I = 17.5 V to 30 V			10	100	mV
		V_I = 20 V to 30 V			3	50	
Ripple rejection	V_I = 18.5 V to 28.5 V, f = 120 Hz	I_O = 100 mA,	T_J = 0°C to 125°C	54			dB
		I_O = 300 mA		54	70		
Output voltage regulation	I_O = 5 mA to 500 mA				25	300	mV
	I_O = 5 mA to 200 mA				10	150	
Temperature coefficient of output voltage	I_O = 5 mA,	T_J = 0°C to 125°C			–1		mV/°C
Output noise voltage	f = 10 Hz to 100 kHz				90		µV
Dropout voltage					2		V
Bias current					4.8	6	mA
Bias current change	V_I = 17.5 V to 30 V,	I_O = 200 mA,	T_J = 0°C to 125°C			0.8	mA
	I_O = 5 mA to 350 mA,	T_J = 0°C to 125°C				0.5	
Short-circuit output current	V_I = 35 V				240		mA
Peak output current					0.7		A

† All characteristics are measured with a 0.33-µF capacitor across the input and a 0.1-µF capacitor across the output. Pulse-testing techniques maintain T_J as close to T_A as possible. Thermal effects must be taken into account separately.

IMPORTANT NOTICE

Texas Instruments and its subsidiaries (TI) reserve the right to make changes to their products or to discontinue any product or service without notice, and advise customers to obtain the latest version of relevant information to verify, before placing orders, that information being relied on is current and complete. All products are sold subject to the terms and conditions of sale supplied at the time of order acknowledgment, including those pertaining to warranty, patent infringement, and limitation of liability.

TI warrants performance of its products to the specifications applicable at the time of sale in accordance with TI's standard warranty. Testing and other quality control techniques are utilized to the extent TI deems necessary to support this warranty. Specific testing of all parameters of each device is not necessarily performed, except those mandated by government requirements.

Customers are responsible for their applications using TI components.

In order to minimize risks associated with the customer's applications, adequate design and operating safeguards must be provided by the customer to minimize inherent or procedural hazards.

TI assumes no liability for applications assistance or customer product design. TI does not warrant or represent that any license, either express or implied, is granted under any patent right, copyright, mask work right, or other intellectual property right of TI covering or relating to any combination, machine, or process in which such products or services might be or are used. TI's publication of information regarding any third party's products or services does not constitute TI's approval, license, warranty or endorsement thereof.

Reproduction of information in TI data books or data sheets is permissible only if reproduction is without alteration and is accompanied by all associated warranties, conditions, limitations and notices. Representation or reproduction of this information with alteration voids all warranties provided for an associated TI product or service, is an unfair and deceptive business practice, and TI is not responsible nor liable for any such use.

Resale of TI's products or services with *statements different from or beyond the parameters* stated by TI for that product or service voids all express and any implied warranties for the associated TI product or service, is an unfair and deceptive business practice, and TI is not responsible nor liable for any such use.

Also see: Standard Terms and Conditions of Sale for Semiconductor Products. www.ti.com/sc/docs/stdterms.htm

Mailing Address:

Texas Instruments
Post Office Box 655303
Dallas, Texas 75265

Copyright © 2001, Texas Instruments Incorporated